

Title (en)

FIELD-EFFECT TRANSISTOR COMPRISING A LEAKAGE-CURRENT LIMITER

Title (de)

FELDEFFEKTTRANSISTOR MIT EINEM LECKSTROMBEGRENZER

Title (fr)

TRANSISTOR A EFFET DE CHAMP COMPRENANT UN LIMITEUR DE COURANT DE FUITE

Publication

**EP 2756532 A1 20140723 (FR)**

Application

**EP 12753770 A 20120730**

Priority

- FR 1158182 A 20110914
- FR 2012051798 W 20120730

Abstract (en)

[origin: WO2013038082A1] This field-effect transistor (1) comprises at least one lower substrate (2) on which substrate the following are deposited: two electrodes (3, 4), respectively a source electrode (3) and a drain electrode (4); a dielectric layer (6) made of a dielectric material; and a gate electrode (7), the latter being deposited on the dielectric layer (6). It comprises an intermediate layer (10) made of a material comprising molecules having a dipolar moment meeting particular orientation criteria, this layer being deposited between the gate electrode (7) and the dielectric layer (6), said intermediate layer (10) at least extending under the entire area occupied by the gate electrode (7), this intermediate layer being made of an organic compound at least having a tie layer function for the gate electrode (7).

IPC 8 full level

**H10K 99/00** (2023.01)

CPC (source: EP US)

**H10K 10/464** (2023.02 - EP US); **H10K 10/474** (2023.02 - EP US); **H10K 71/00** (2023.02 - US)

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)

**FR 2980041 A1 20130315; FR 2980041 B1 20160205**; EP 2756532 A1 20140723; US 2014183513 A1 20140703; US 9112160 B2 20150818; WO 2013038082 A1 20130321

DOCDB simple family (application)

**FR 1158182 A 20110914**; EP 12753770 A 20120730; FR 2012051798 W 20120730; US 201414200577 A 20140307